



SLLS558C-DECEMBER 2002-REVISED JANUARY 2007

MULTIPOINT-LVDS LINE DRIVER AND RECEIVER

FEATURES

- Low-Voltage Differential 30-Ω to 55-Ω Line Drivers and Receivers for Signaling Rates⁽¹⁾ Up to 200 Mbps
- Type-1 Receivers Incorporate 25 mV of Hysteresis
- Type-2 Receivers Provide an Offset (100 mV) Threshold to Detect Open-Circuit and Idle-Bus Conditions
- Meets or Exceeds the M-LVDS Standard TIA/EIA-899 for Multipoint Data Interchange
- Controlled Driver Output Voltage Transition Times for Improved Signal Quality
- -1 V to 3.4 V Common-Mode Voltage Range Allows Data Transfer With 2 V of Ground Noise
- Bus Pins High Impedance When Disabled or $V_{CC} \le 1.5 \text{ V}$
- 100-Mbps Devices Available (SN65MLVD200A, 202A, 204A, 205A)
- M-LVDS Bus Power Up/Down Glitch Free

The signaling rate of a line, is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

APPLICATIONS

- Low-Power High-Speed Short-Reach Alternative to TIA/EIA-485
- Backplane or Cabled Multipoint Data and Clock Transmission
- Cellular Base Stations
- Central-Office Switches
- Network Switches and Routers

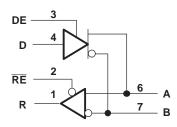
DESCRIPTION

The SN65MLVD201, 203, 206, and 207 are multipoint-low-voltage differential (M-LVDS) line drivers and receivers, which are optimized to operate at signaling rates up to 200 Mbps. All parts comply with the multipoint low-voltage differential signaling (M-LVDS) standard TIA/EIA-899. These circuits are similar to their TIA/EIA-644 standard compliant LVDS counterparts, with added features to address multipoint applications. The driver output has been designed to support multipoint buses presenting loads as low as 30 Ω , and incorporates controlled transition times to allow for stubs off of the backbone transmission line.

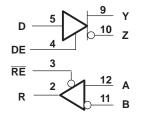
These devices have Type-1 and Type-2 receivers that detect the bus state with as little as 50 mV of differential input voltage over a common-mode voltage range of -1 V to 3.4 V. The Type-1 receivers exhibit 25 mV of differential input voltage hysteresis to prevent output oscillations with slowly changing signals or loss of input. Type-2 receivers include an offset threshold to provide a known output state under open-circuit, idle-bus, and other faults conditions. The devices are characterized for operation from -40° C to 85°C.

LOGIC DIAGRAM (POSITIVE LOGIC)

SN65MLVD201, SN65MLVD206



SN65MLVD203, SN65MLVD207





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

PART NUMBER ⁽¹⁾	FOOTPRINT	RECEIVER TYPE	PACKAGE MARKING
SN65MLVD201D	SN75176	Type 1	MF201
SM65MLVD203D	SN75ALS180	Type 1	MLVD203
SN65MLVD206D	SN75176	Type 2	MF206
SM65MLVD207D	SN75ALS180	Type 2	MLVD207

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI (1) website at www.ti.com.

PACKAGE DISSIPATION RATINGS

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 85°C POWER RATING
D(8)	725 mW	5.8 mW/°C	377 mW
D(14)	950 mW	7.6 mW/°C	494 mw

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			VALUE / UNIT
Supply voltage range ⁽²⁾ ,	V _{CC}		–0.5 V to 4 V
	D, DE, RE		–0.5 V to 4 V
Input voltage range	A, B (201, 206)	-1.8 V to 4 V	
	A, B (203, 207)	-4 V to 6 V	
	R		-0.3 V to 4 V
Output voltage range	Y, Z, A, or B		-1.8 V to 4 V
	Human Body Model ⁽³⁾	A, B, Y, and Z	±8 kV
Electrostatic discharge	Furnari Bouy Model	All pins	±2 kV
	Charged-Device Model ⁽⁴⁾	All pins	±1500 V
Continuous power dissip	ation		See Dissipation Rating Table
Storage temperature ran	ge		–65°C to 150°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

(3)

Tested in accordance with JEDEC Standard 22, Test Method A114-A. Tested in accordance with JEDEC Standard 22, Test Method C101. (4)

RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	3	3.3	3.6	V
V_{IH}	High-level input voltage	2		V_{CC}	V
V_{IL}	Low-level input voltage	GND		0.8	V
	Voltage at any bus terminal V_A , V_B , V_Y or V_Z	-1.4		3.8	V
$ V_{ID} $	Magnitude of differential input voltage	0.05		V_{CC}	V
T _A	Operating free-air temperature	-40		85	°C

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DEVICE ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		ETER	TEST CONDITIONS	MIN TYP ⁽¹⁾	MAX	UNIT
		Driver only	$\overline{\text{RE}}$ and DE at V _{CC} , R _L = 50 Ω , All others open	13	22	
	0	Both disabled	\overline{RE} at V _{CC} , DE at 0 V, R _L = No Load, All others open	1	4	~ ^
ICC	Supply current	Both enabled	\overline{RE} at 0 V, DE at V _{CC} , R _L = 50 Ω , All others open	16	24	mA
		Receiver only	$\overline{\text{RE}}$ at 0 V, DE at 0 V, R _L = 50 Ω , All others open	4	13	

(1) All typical values are at 25°C and with a 3.3-V supply voltage.

DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN ⁽¹⁾	TYP ⁽²⁾ MAX	UNIT
V _{AB} or V _{YZ}	Differential output voltage magnitude	See Figure 2	480	650	mV
$\begin{array}{c} \Delta V_{AB} \text{ or } \\ \Delta V_{YZ} \end{array}$	Change in differential output voltage magnitude between logic states		-50	50	mV
V _{OS(SS)}	Steady-state common-mode output voltage		0.8	1.2	V
$\Delta V_{OS(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 3	-50	50	mV
V _{OS(PP)}	Peak-to-peak common-mode output voltage			150	mV
$V_{Y(OC)} \text{ or } \\ V_{A(OC)}$	Maximum steady-state open-circuit output voltage	See Figure 7	0	2.4	V
$V_{Z(OC)} \text{ or } \\ V_{B(OC)}$	Maximum steady-state open-circuit output voltage		0	2.4	V
V _{P(H)}	Voltage overshoot, low-to-high level output	See Figure 5		1.2 V _{SS}	V
V _{P(L)}	Voltage overshoot, high-to-low level output	See Figure 5	-0.2 V _{SS}		V
I _{IH}	High-level input current (D, DE)	$V_{IH} = 2 V$	0	10	μA
IIL	Low-level input current (D, DE)	$V_{IL} = 0.8 V$	0	10	μA
JI _{OS} J	Differential short-circuit output current magnitude	See Figure 4		24	mA
I _{OZ}	High-impedance state output current (driver only)	$-1.4 \text{ V} \le \text{V}_{\text{Y}} \text{ or } \text{V}_{\text{Z}} \le 3.8 \text{ V},$ Other output = 1.2 V	-15	10	μA
I _{O(OFF)}	Power-off output current	$\begin{array}{l} -1.4 \text{ V} \leq \text{V}_{\text{Y}} \text{ or } \text{V}_{Z} \leq 3.8 \text{ V},\\ \text{Other output} = 1.2 \text{ V},\\ 0 \text{ V} \leq \text{V}_{\text{CC}} \leq 1.5 \text{ V} \end{array}$	-10	10	μA
$C_{Y} \text{ or } C_{Z}$	Output capacitance	$V_I = 0.4 \sin(30E6\pi t) + 0.5 V$, ⁽³⁾ Other input at 1.2 V, Driver disabled		3	pF
C _{YZ}	Differential output capacitance	$V_{AB} = 0.4 \sin(30E6\pi t) V$, ⁽³⁾ Driver disabled		2.5	pF
C _{Y/Z}	Output capacitance balance, (C_Y/C_Z)		0.99	1.01	

(1) The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

(2) All typical values are at 25°C and with a 3.3-V supply voltage.

(3) HP4194A impedance analyzer (or equivalent)

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RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted⁽¹⁾

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V	Depitive going differential input valtage threshold	Type 1				50	m)/
V _{IT+}	Positive-going differential input voltage threshold	Type 2				150	mV
V	Negative going differential input voltage threshold	Type 1	See Figure 9 and Table 1 and	-50			mV
V _{IT-}	Negative-going differential input voltage threshold		Table 2	50			mv
V	Differential input voltage hysteresis, (V _{IT+} – V _{IT})	Type 1			25		mV
V _{HYS}	Differential input voltage hysteresis, $(v_{\text{IT}+} - v_{\text{IT}})$	Type 2			0		mv
V _{OH}	High-level output voltage		$I_{OH} = -8 \text{ mA}$	2.4			V
V _{OL}	Low-level output voltage		I _{OL} = 8 mA			0.4	V
I _{IH}	High-level input current (RE)		$V_{IH} = 2 V$	-10		0	μΑ
IIL	Low-level input current (RE)		$V_{IL} = 0.8 V$	-10		0	μΑ
I _{OZ}	High-impedance output current		$V_{O} = 0 V \text{ or } 3.6 V$	-10		15	μΑ
$C_A \text{ or } C_B$	C _A or C _B Input capacitance		$V_{I} = 0.4 \sin(30E6\pi t) + 0.5 V$, ⁽²⁾ Other input at 1.2 V		3		pF
C _{AB}	B Differential input capacitance		$V_{AB} = 0.4 \sin(30E6\pi t) V^{(2)}$			2.5	pF
C _{A/B}	Input capacitance balance, (C _A ,C _B)			0.99		1.01	

All typical values are at 25°C and with a 3.3-V supply voltage.
 HP4194A impedance analyzer (or equivalent)

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BUS INPUT AND OUTPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾ MAX	UNIT
		$V_A = 3.8 V,$ $V_B = 1.2 V,$	0	32	
I _A	Receiver or transceiver with driver disabled input current	$V_A = 0 V \text{ or } 2.4 V, V_B = 1.2 V$	-20	20	μA
		$V_{A} = -1.4 \text{ V}, \qquad V_{B} = 1.2 \text{ V}$	-32	0	
		$V_B = 3.8 V$, $V_A = 1.2 V$	0	32	
I _B	Receiver or transceiver with driver disabled input current	$V_B = 0 V \text{ or } 2.4 V, V_A = 1.2 V$	-20	20	μA
		$V_B = -1.4 V$, $V_A = 1.2 V$	-32	0	
I _{AB}	Receiver or transceiver with driver disabled differential input current $(I_A - I_B)$	$V_{A} = V_{B}, \qquad 1.4 \le V_{A} \le 3.8 \text{ V}$	-4	4	μΑ
		$V_A = 3.8 \text{ V},$ $V_B = 1.2 \text{ V},$ $0 \text{ V} \leq V_{CC}$	≤ 1.5 V 0	32	
I _{A(OFF)}	Receiver or transceiver power-off input current	$V_A = 0 \text{ V or } 2.4 \text{ V}, V_B = 1.2 \text{ V}, 0 \text{ V} \leq V_{CC}$	≤ 1.5 V –20	20	μΑ
		$V_{\text{A}} = -1.4 \text{ V}, \qquad \qquad V_{\text{B}} = 1.2 \text{ V}, \qquad 0 \text{ V} \leq \text{V}_{\text{CC}}$	≤ 1.5 V –32	0	
		$V_{B} = 3.8 \text{ V}, \qquad \qquad V_{A} = 1.2 \text{ V}, \qquad 0 \text{ V} \leq V_{CC}$	≤ 1.5 V 0	32	
I _{B(OFF)}	Receiver or transceiver power-off input current	$V_{B} = 0 \text{ V or } 2.4 \text{ V}, \qquad V_{A} = 1.2 \text{ V}, \qquad 0 \text{ V} \leq V_{CC}$	≤ 1.5 V –20	20	μA
		$V_{B} = -1.4 \text{ V}, \qquad \qquad V_{A} = 1.2 \text{ V}, \qquad 0 \text{ V} \leq V_{CC}$	≤ 1.5 V –32	0	
I _{AB(OFF)}	Receiver input or transceiver power-off differential input current $(I_A - I_B)$	$V_A = V_B, 0 V \le V_{CC} \le 1.5 V, -1.4 \le V_A \le 3.8 V$	-4	4	μΑ
C _A	Transceiver with driver disabled input capacitance	$V_A = 0.4 \sin (30E6\pi t) + 0.5V^{(2)}, V_B = 1.2 V_B$	/	5	pF
C _B	Transceiver with driver disabled input capacitance	$V_B = 0.4 \sin (30E6\pi t) + 0.5 V^{(2)}, V_A = 1.2 V_A$	/	5	pF
C _{AB}	Transceiver with driver disabled differential input capacitance	V _{AB} = 0.4 sin (30E6πt)V ⁽²⁾		3	pF
C _{A/B}	Transceiver with driver disabled input capacitance balance, (C_A/C_B)		0.99	1.01	

(1) All typical values are at 25° C and with a 3.3-V supply voltage.

(2) HP4194A impedance analyzer (or equivalent)

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAN	IETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		1	1.5	2.4	ns
t _{PHL}	Propagation delay time, high-to-low-level output		1	1.5	2.4	ns
t _r	Differential output signal rise time		1		1.6	ns
t _f	Differential output signal fall time	See Figure 5	1		1.6	ns
t _{sk(p)}	Pulse skew (t _{PHL} – t _{PLH})			0	100	ps
t _{sk(pp)}	Part-to-part skew ⁽²⁾				1	ns
t _{jit(per)}	Period jitter, rms (1 standard deviation) ⁽³⁾	100 MHz clock input ⁽⁴⁾		2	3	ps
t _{jit(pp)}	Peak-to-peak jitter ^{(3) (5)}	200 Mbps 2 ¹⁵ –1 PRBS input ⁽⁶⁾		30	130	ps
t _{PHZ}	Disable time, high-level-to-high-impedance output				7	ns
t _{PLZ}	Disable time, low-level-to-high-impedance output				7	ns
t _{PZH}	Enable time, high-impedance-to-high-level output	See Figure 6			7	ns
t _{PZL}	Enable time, high-impedance-to-low-level output				7	ns

(1) All typical values are at 25°C and with a 3.3-V supply voltage.

(2) t_{sk(pp)} is the magnitude of the time difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

(3) Jitter is ensured by design and characterization. Stimulus jitter has been subtracted from the numbers.

(4) $t_r = t_f = 0.5$ ns (10% to 90%), measured over 30 k samples.

(5) Peak-to-peak jitter includes jitter due to pulse skew $(t_{sk(p)})$.

(6) $t_r = t_f = 0.5$ ns (10% to 90%), measured over 100 k samples.

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RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t _{pLH}	Propagation delay time, low-to-high-level output			2	4	6	ns
t _{pHL}	Propagation delay time, high-to-low-level output			2	4	6	ns
t _r	Output signal rise time			1		2.3	ns
t _f	Output signal fall time		$C_L = 15 \text{ pF}$, See Figure 10	1		2.3	ns
		Type 1			100	300	ps
t _{sk(p)}	Pulse skew (t _{pHL} - t _{pLH})	Type 2			300	500	ps
t _{sk(pp)}	Part-to-part skew ⁽²⁾					1	ns
t _{jit(per)}	Period jitter, rms (1 standard deviation) (3)		100 MHz clock input ⁽⁴⁾		4	7	ps
	Deck to peak iitter(3)(5)	Type 1	000 Million 015 4 DDD0 innot(6)		300	700	ps
t _{jit(pp)}	Peak-to-peak jitter (3)(5)	Type 2	200 Mbps 2 ¹⁵ –1 PRBS input ⁽⁶⁾		450	800	ps
t _{pHZ}	Disable time, high-level-to-high-impedance output					10	ns
t _{pLZ}	Disable time, low-level-to-high-impedance output					10	ns
t _{pZH}	Enable time, high-impedance-to-high-level output		See Figure 11			15	ns
t _{pZL}	Enable time, high-impedance-to-low-level output					15	ns

(1) All typical values are at 25°C and with a 3.3-V supply voltage.

tsk(pp) is the magnitude of the time difference in propagation delay times between any specified terminals of two devices when both (2) $V_{ID} = 200 \text{ mV}_{pp}$ (LVD201, 203), $V_{ID} = 400 \text{ mV}_{pp}$ (LVD206, 207), $V_{cm} = 1 \text{ V}$, $t_r = t_f = 0.5 \text{ ns}$ (10% to 90%), measured over 30 k samples.

(3)

(4)

(5)

6

Peak-to-peak jitter includes jitter due to pulse skew ($t_{sk(p)}$). V_{ID} = 200 mV_{pp} (LVD201, 203), V_{ID} = 400 mV_{pp} (LVD206, 207), V_{cm} = 1 V, t_r = t_f = 0.5 ns (10% to 90%), measured over 100 k samples. (6)

PARAMETER MEASUREMENT INFORMATION

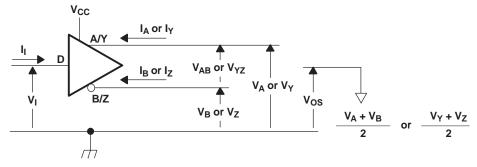
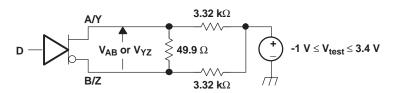
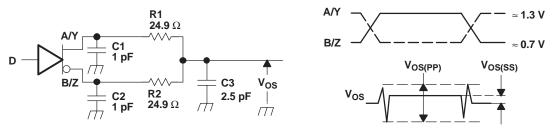


Figure 1. Driver Voltage and Current Definitions



A. All resistors are 1% tolerance.

Figure 2. Differential Output Voltage Test Circuit



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, pulse frequency = 500 kHz, duty cycle = 50 ± 5%.
- B. C1, C2 and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20%.
- C. R1 and R2 are metal film, surface mount, 1%, and located within 2 cm of the D.U.T.
- D. The measurement of $V_{OS(PP)}$ is made on test equipment with a –3 dB bandwidth of at least 1 GHz.

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

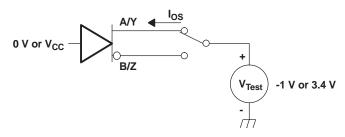
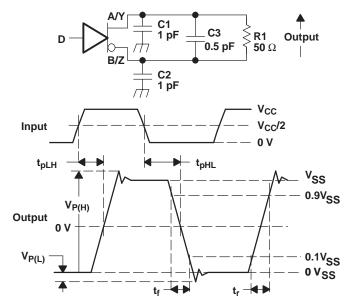


Figure 4. Driver Short-Circuit Test Circuit

Product Folder Link(s): SN65MLVD201 SN65MLVD203 SN65MLVD206 SN65MLVD207

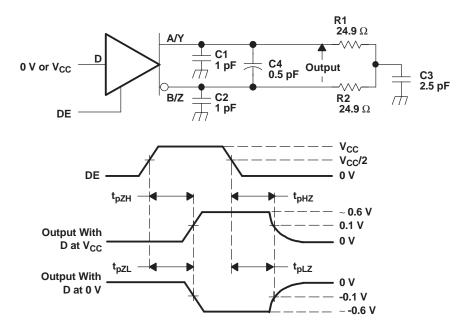
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PARAMETER MEASUREMENT INFORMATION (continued)



- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, frequency = 500 kHz, duty cycle = 50 5%.
- B. C1, C2, and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20%.
- C. R1 is a metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
- D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

Figure 5. Driver Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal

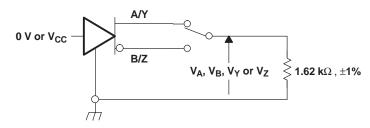


- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, frequency = 500 kHz, duty cycle = 50 5%.
- B. C1, C2, C3, and C4 includes instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20%.
- C. R1 and R2 are metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
- D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

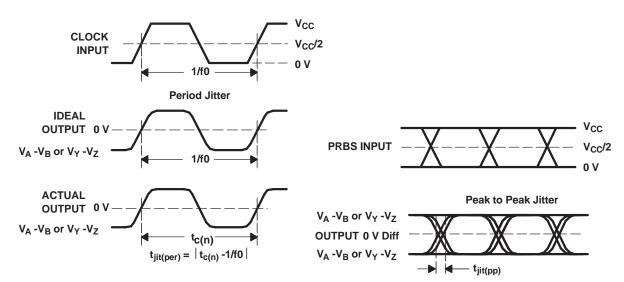
Figure 6. Driver Enable and Disable Time Circuit and Definitions



PARAMETER MEASUREMENT INFORMATION (continued)







A. All input pulses are supplied by an Agilent 8304A Stimulus System.

B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software

C. Period jitter is measured using a 100 MHz 50 1% duty cycle clock input.

D. Peak-to-peak jitter is measured using a 200Mbps 2¹⁵-1 PRBS input.

Figure 8. Driver Jitter Measurement Waveforms

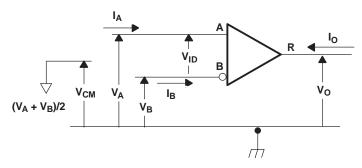


Figure 9. Receiver Voltage and Current Definitions

Product Folder Link(s): SN65MLVD201 SN65MLVD203 SN65MLVD206 SN65MLVD207

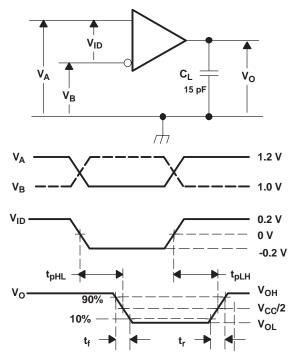
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APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON- MODE INPUT VOLTAGE	RECEIVER OUTPUT ⁽¹⁾			
VIA	V _{IA} V _{IB} V _{ID}		V _{IC}				
2.400	0.000	2.400	1.200	Н			
0.000	2.400	-2.400	1.200	L			
3.800	3.750	0.050	3.775	Н			
3.750	3.800	-0.050	3.775	L			
-1.350	-1.400	0.050	-1.375	Н			
-1.400	-1.350	-0.050	-1.375	L			

(1) H = high level, L = low level, output state assumes receiver is enabled ($\overline{RE} = L$)

APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON- MODE INPUT VOLTAGE	RECEIVER OUTPUT ⁽¹⁾
VIA	V _{IB}	V _{ID}	V _{IC}	OUIPUI
2.400	0.000	2.400	1.200	Н
0.000	2.400	-2.400	1.200	L
3.800	3.650	0.150	3.725	Н
3.800	3.750	0.050	3.775	L
-1.250	-1.400	0.150	-1.325	Н
-1.350	-1.400	0.050	-1.375	L

(1) $H = high level, L = low level, output state assumes receiver is enabled (<math>\overline{RE} = L$)

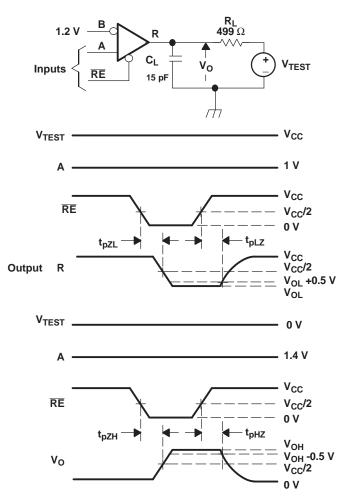


- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, frequency = 50 MHz, duty cycle = 50 5%. C_L is a combination of a 20%-tolerance, low-loss ceramic, surface-mount capacitor and fixture capacitance within 2 cm of the D.U.T.
- B. The measurement is made on test equipment with a –3 dB bandwidth of at least 1 GHz.

Figure 10. Receiver Timing Test Circuit and Waveforms

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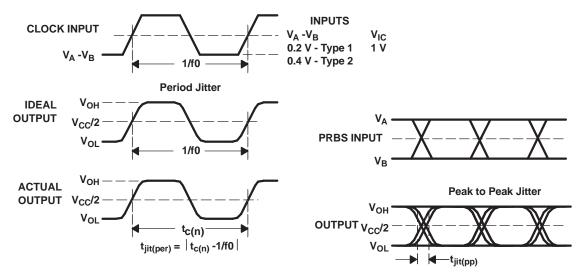


- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 1$ ns, frequency = 500 kHz, duty cycle = 50 5%.
- B. R_L is 1% tolerance, metal film, surface mount, and located within 2 cm of the D.U.T.
- C. R_L is 1% tolerance, metal film, surface mount, and located within 2 cm of the D.U.T.
- D. C_L is the instrumentation and fixture capacitance within 2 cm of the DUT and 20%.

Figure 11. Receiver Enable/Disable Time Test Circuit and Waveforms

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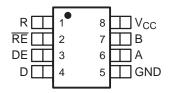


- A. All input pulses are supplied by an Agilent 8304A Stimulus System.
- B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software
- C. Period jitter is measured using a 100 MHz 50 1% duty cycle clock input.
- D. Peak-to-peak jitter is measured using a 200 Mbps 2¹⁵-1 PRBS input.

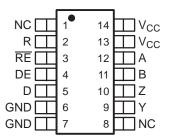
Figure 12. Receiver Jitter Measurement Waveforms

PIN ASSIGNMENTS









NC - No internal connection



DEVICE FUNCTION TABLES

TYPE-1 RECEIVER (201, 203)							
INPUTS	INPUTS						
$V_{ID} = V_A - V_B$	RE	R					
V _{ID} ≥50 mV	L	Н					
-50 mV < V _{ID} < 50 mV	L	?					
V _{ID} ≤ -50 mV	L	L					
Х	Н	Z					
Х	Open	Z					
Open Circuit	L	?					

TYPE-2 RECEIVER (206, 207)

INPUTS	OUTPUT	
$V_{ID} = V_A - V_B$	RE	R
V _{ID} ≥ 150 mV	L	Н
50 mV < V _{ID} < 150 mV	L	?
$V_{ID} \le 50 \text{ mV}$	L	L
Х	Н	Z
Х	Open	Z
Open Circuit	L	L

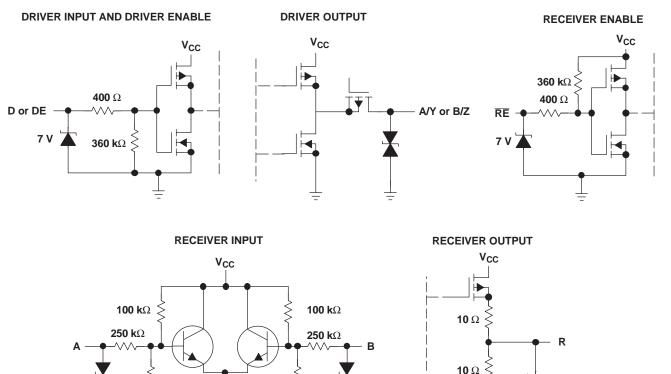
DRIVER

INPUT	ENABLE	OUTPUTS				
D	DE	A OR Y	B OR Z			
L	Н	L	Н			
н	Н	Н	L			
OPEN	Н	L	Н			
X	OPEN	Z	Z			
Х	L	Z	Z			

H = high level, L = low level, Z = high impedance, X = Don't care, ? = indeterminate

EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

200 kΩ



Copyright © 2002–2007, Texas Instruments Incorporated Submit Documentation Feedback Product Folder Link(s): SN65MLVD201 SN65MLVD203 SN65MLVD206 SN65MLVD207

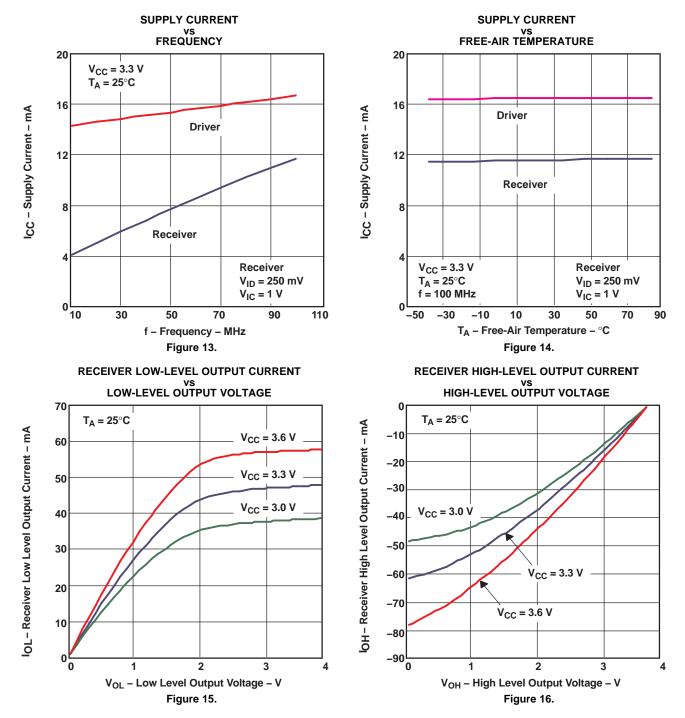
200 kΩ

7 V

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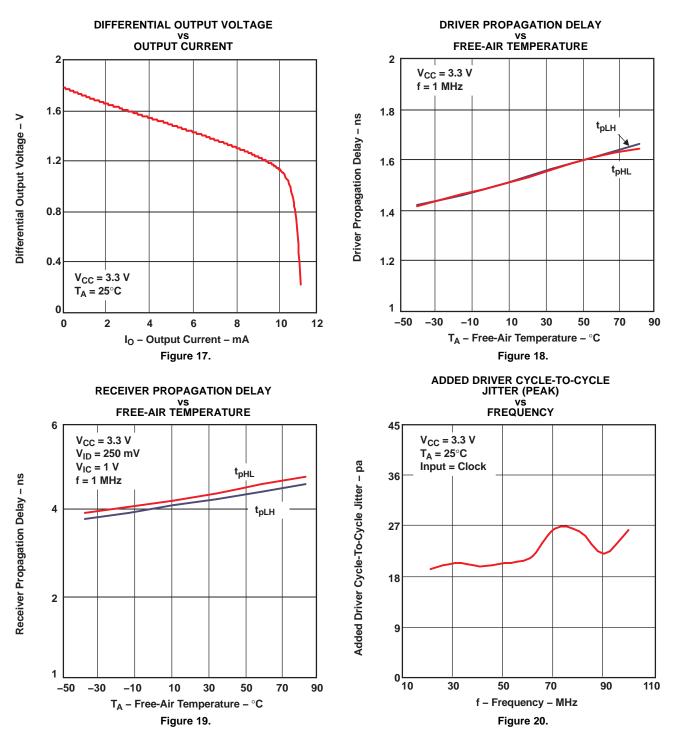
TYPICAL CHARACTERISTICS



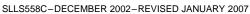


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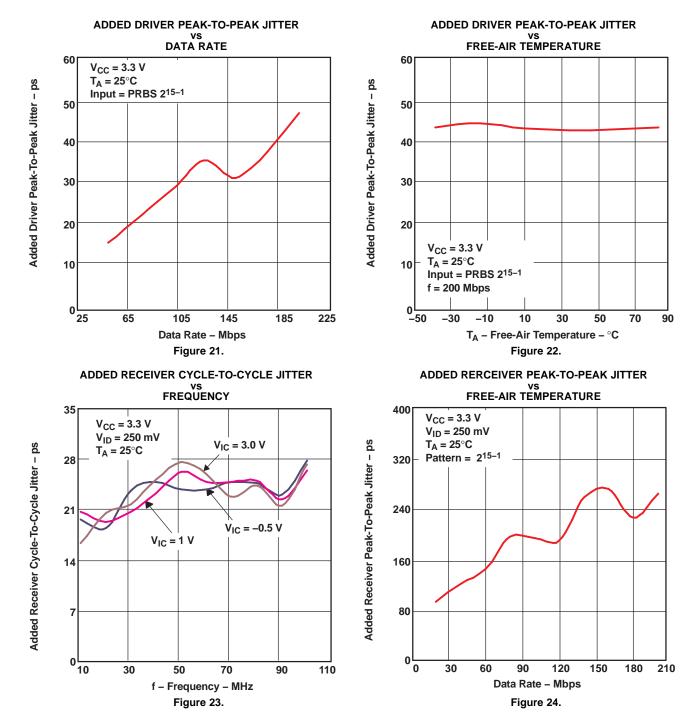


TYPICAL CHARACTERISTICS (continued)





TYPICAL CHARACTERISTICS (continued)

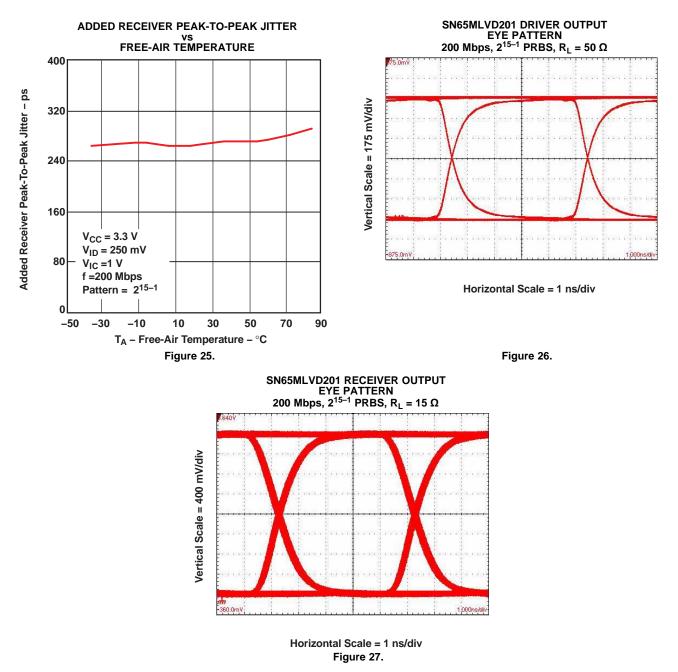




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TYPICAL CHARACTERISTICS (continued)



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APPLICATION INFORMATION

Receiver Input Threshold (Failsafe)

The MLVD standard defines a type 1 and type 2 receiver. Type 1 receivers include no provisions for failsafe and have their differential input voltage thresholds near zero volts. Type 2 receivers have their differential input voltage thresholds offset from zero volts to detect the absence of a voltage difference. The impact to receiver output by the offset input can be seen in Table 3 and Figure 28.

Table 3. Receiver Input Voltage Threshold Requirements

RECEIVER TYPE	OUTPUT LOW	OUTPUT HIGH
Type 1	$-2.4 \text{ V} \le \text{V}_{\text{ID}} \le -0.05 \text{ V}$	$0.05 \text{ V} \leq \text{V}_{\text{ID}} \leq 2.4 \text{ V}$
Type 2	$-2.4 \text{ V} \le \text{V}_{\text{ID}} \le 0.05 \text{ V}$	$0.15 \text{ V} \le \text{V}_{\text{ID}} \le 2.4 \text{ V}$

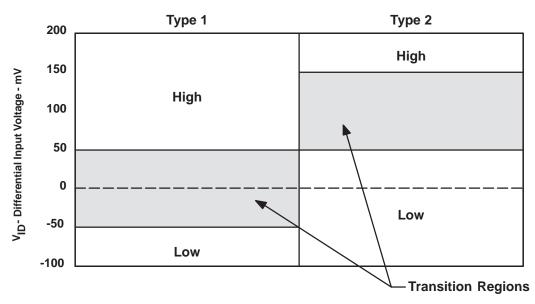


Figure 28. Expanded Graph of Receiver Differential Input Voltage Showing Transition Region

LIVE INSERTION/GLITCH-FREE POWER UP/DOWN

The SN65MLVD201/203/206/207 family of products offered by Texas Instruments provides a glitch-free powerup/down feature that prevents the M-LVDS outputs of the device from turning on during a powerup or powerdown event. This is especially important in live insertion applications, when a device is physically connected to an M-LVDS multipoint bus and VCC is ramping.

While the M-LVDS interface for these devices is glitch free on powerup/down, the receiver output structure is not.Figure 29 shows the performance of the receiver output pin, R (CHANNEL 2), as Vcc (CHANNEL 1) is ramped.

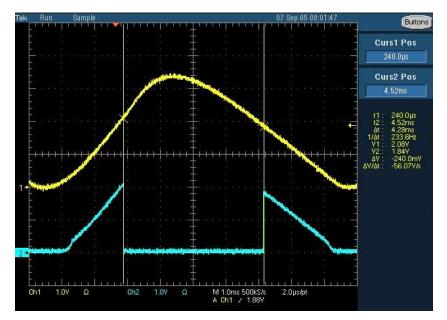


Figure 29. M-LVDS Receiver Output: VCC (CHANNEL 1), R Pin (CHANNEL 2)

The glitch on the R pin is independent of the \overline{RE} voltage. Any complications or issues from this glitch are easily resolved in power sequencing or system requirements that suspend operation until VCC has reached a steady state value.



PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN65MLVD201D	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF201
SN65MLVD201D.B	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF201
SN65MLVD201DG4	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF201
SN65MLVD201DR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF201
SN65MLVD201DR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF201
SN65MLVD203D	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD203
SN65MLVD203D.B	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD203
SN65MLVD203DG4	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD203
SN65MLVD203DR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD203
SN65MLVD203DR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD203
SN65MLVD203DRG4.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD203
SN65MLVD206D	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF206
SN65MLVD206D.B	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF206
SN65MLVD206DG4	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF206
SN65MLVD206DR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF206
SN65MLVD206DR.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF206
SN65MLVD206DRG4.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MF206
SN65MLVD207D	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD207
SN65MLVD207D.B	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD207
SN65MLVD207DG4	Active	Production	SOIC (D) 14	50 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD207
SN65MLVD207DR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD207
SN65MLVD207DR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD207
SN65MLVD207DRG4.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD207

⁽¹⁾ **Status:** For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.



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⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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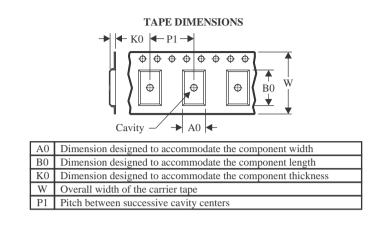


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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



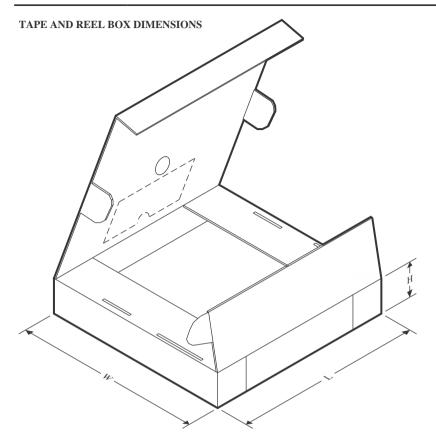
*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65MLVD201DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65MLVD203DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN65MLVD206DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65MLVD207DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



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PACKAGE MATERIALS INFORMATION

23-May-2025



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65MLVD201DR	SOIC	D	8	2500	353.0	353.0	32.0
SN65MLVD203DR	SOIC	D	14	2500	333.2	345.9	28.6
SN65MLVD206DR	SOIC	D	8	2500	353.0	353.0	32.0
SN65MLVD207DR	SOIC	D	14	2500	340.5	336.1	32.0

TEXAS INSTRUMENTS

SN65MLVD207D.B

SN65MLVD207DG4

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T (µm)

3940

3940

3940

3940

3940

3940

3940

3940

3940

3940

3940

3940

8

8

B (mm)

4.32

4.32

4.32

4.32

4.32

4.32

4.32

4.32

4.32

4.32

4.32

4.32

23-May-2025

TUBE



B - Alignment groove width

*All dimensions are nominal						
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)
SN65MLVD201D	D	SOIC	8	75	507	8
SN65MLVD201D.B	D	SOIC	8	75	507	8
SN65MLVD201DG4	D	SOIC	8	75	507	8
SN65MLVD203D	D	SOIC	14	50	507	8
SN65MLVD203D.B	D	SOIC	14	50	507	8
SN65MLVD203DG4	D	SOIC	14	50	507	8
SN65MLVD206D	D	SOIC	8	75	507	8
SN65MLVD206D.B	D	SOIC	8	75	507	8
SN65MLVD206DG4	D	SOIC	8	75	507	8
SN65MLVD207D	D	SOIC	14	50	507	8

SOIC

SOIC

14

14

50

50

507

507

D

D

D0014A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



D0014A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0014A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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